



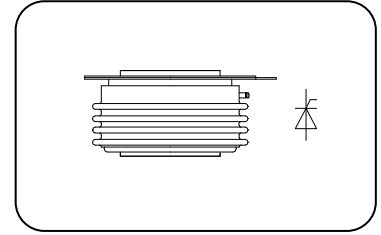
**Features**

- Interdigitated amplifying gates
- Fast turn-on and high di/dt
- Low switching losses

**Typical Applications**

- Inductive heating
- Electronic welders
- Self-commutated inverters

**$I_{T(AV)}$  2000A**  
 **$V_{DRM}/V_{RRM}$  1900~2200V**  
 **$t_q$  22~42 $\mu$ s**  
 **$I_{TSM}$  23 kA**  
 **$I^2t$  2645 10<sup>3</sup>A<sup>2</sup>S**



SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T <sub>j</sub> (°C)	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled, T <sub>C</sub> =55°C	125		2000	2240	A
$V_{DRM}$ $V_{RRM}$	Repetitive peak off-state voltage Repetitive peak reverse voltage	$V_{DRM}&V_{RRM}$ , tp=10ms $V_{DSM}&V_{RSM}=V_{DRM}&V_{RRM}+100V$	125	1900		2200	V
$I_{DRM}$ $I_{RRM}$	Repetitive peak current	$V_D=V_{DRM}$ $V_R=V_{RRM}$	125			160	mA
$I_{TSM}$	Surge on-state current	10ms half sine wave	125			23	kA
$I^2t$	I <sup>2</sup> T for fusing coordination					2645	A <sup>2</sup> s*10 <sup>3</sup>
$V_{TO}$	Threshold voltage		125			1.45	V
$r_T$	On-state slop resistance					0.21	mΩ
$V_{TM}$	Peak on-state voltage	I <sub>TM</sub> =4000A, F=35kN	25			3.15	V
dv/dt	Critical rate of rise of off-state voltage	V <sub>DM</sub> =0.67V <sub>DRM</sub>	125			1000	V/μs
di/dt	Critical rate of rise of on-state current	V <sub>DM</sub> = 67%V <sub>DRM</sub> , I <sub>TM</sub> =(2-3)I <sub>T(AV)</sub> ,t=5s, Gate pulse t <sub>r</sub> ≤0.5μs I <sub>GM</sub> =1.5A f=50Hz	125			600	A/μs
Q <sub>rr</sub>	Recovery charge	I <sub>TM</sub> =2000A,tp=1000μs, di/dt=-20A/μs,V <sub>R</sub> =100V	125		900		μC
t <sub>q</sub>	Circuit commutated turn-off time	I <sub>TM</sub> =2000A,tp=1000μs, V <sub>R</sub> =100V dv/dt=30V/μs , di/dt=-20A/μs	125	22		42	μs
I <sub>GT</sub>	Gate trigger current	V <sub>A</sub> =12V, I <sub>A</sub> =1A	25	40		250	mA
V <sub>GT</sub>	Gate trigger voltage			0.9		2.5	V
I <sub>H</sub>	Holding current			20		400	mA
V <sub>GD</sub>	Non-trigger gate voltage	V <sub>DM</sub> =67%V <sub>DRM</sub>	125			0.3	V
R <sub>th(j-c)</sub>	Thermal resistance Junction to case	At 180° sine double side cooled Clamping force 35kN				0.012	°C /W
R <sub>th(c-h)</sub>	Thermal resistance case to heat sink					0.003	
F <sub>m</sub>	Mounting force			30		40	kN
T <sub>stg</sub>	Stored temperature			-40		140	°C
W <sub>t</sub>	Weight				900/1190		g
Outline	KT75cT/dT						

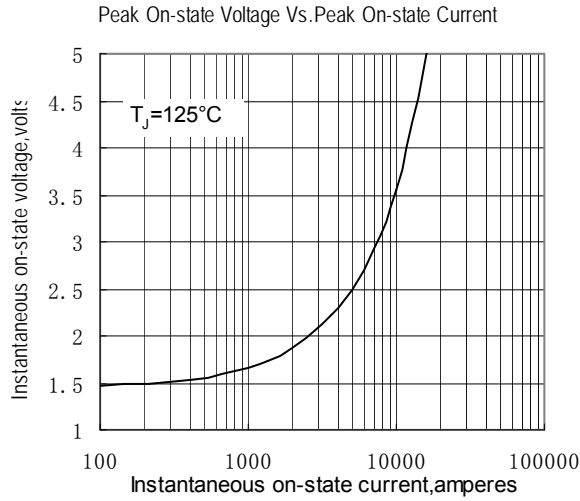


Fig.1

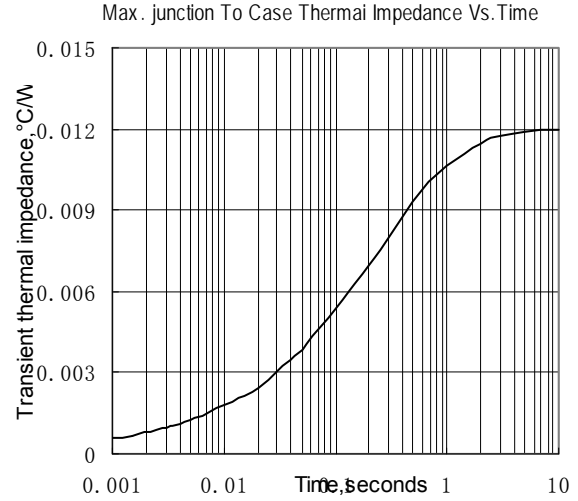


Fig.2

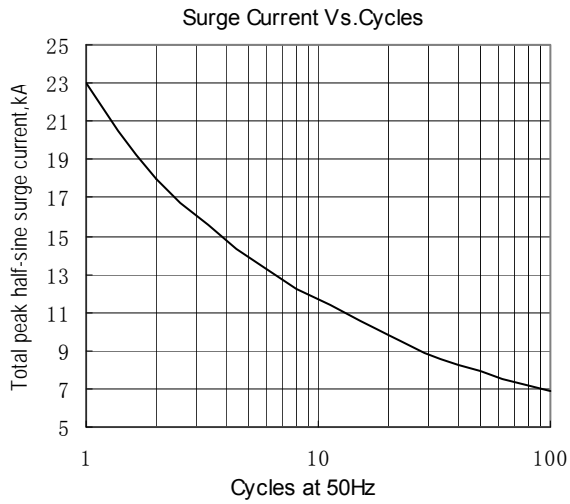


Fig.3

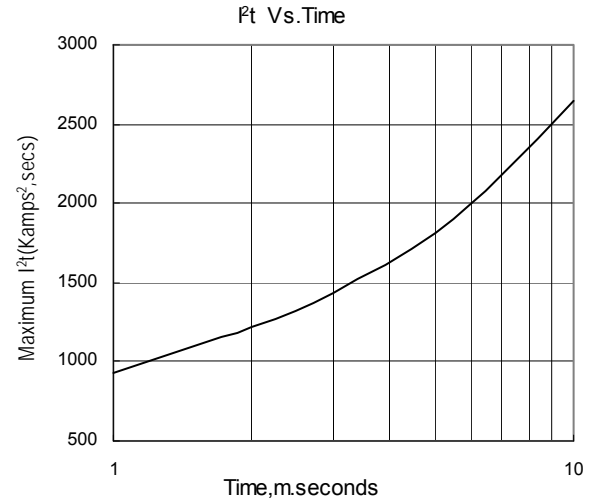


Fig.4

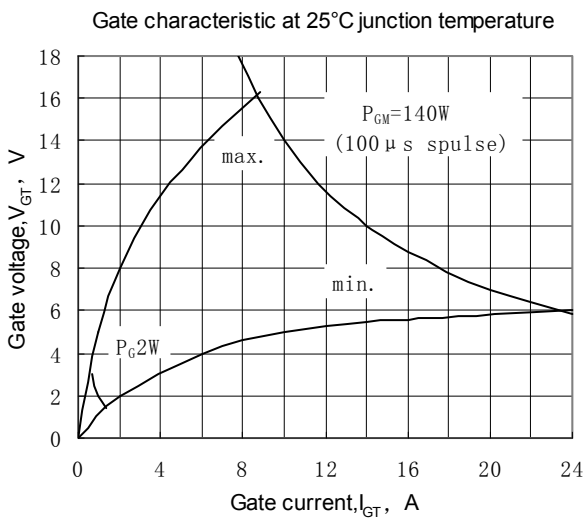


Fig.5

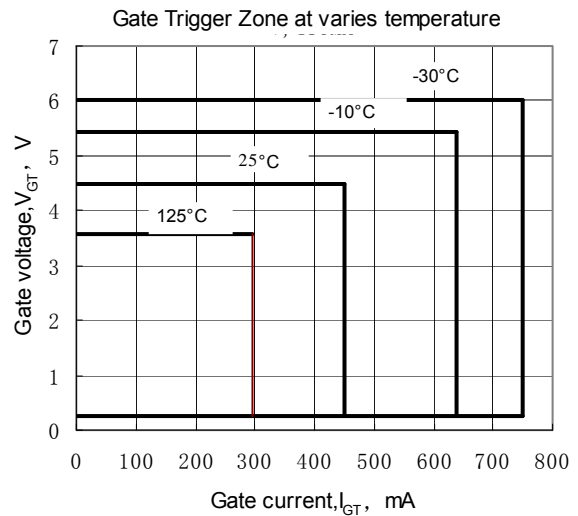


Fig.6



**Outline:**

图14-KT75cT

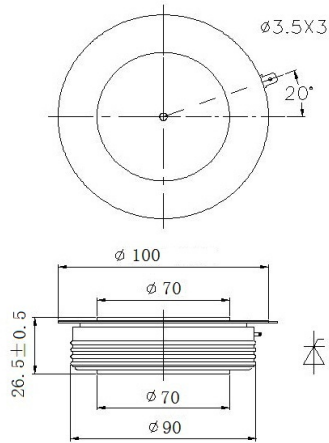
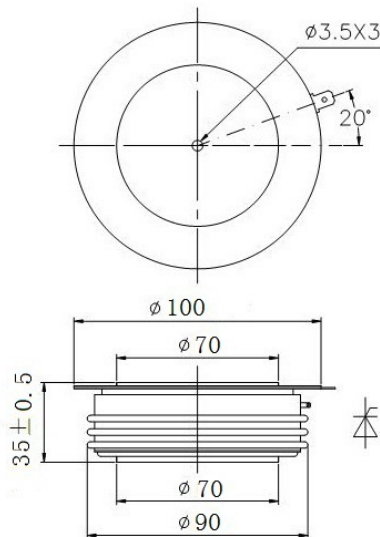


图15-KT75dT



地 址 Address: 辽宁省锦州市滨海新区黔江街21号

邮 编 Zipcode: 121007

电 话 Telephone: 0416-2936666 18840127688

传 真 Fax: 0416-2936888

网 址 Web Sit: <http://www.power-semi.com>

电子邮箱 Email: 13904168481@126.com